

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF1000MB** is Designed for Class A, DME/TACAN Applications up to 1090 MHz.

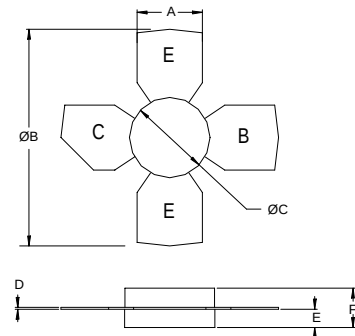
FEATURES:

- Class A Operation
- $P_G = 10$ dB at 0.2 W/1090 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	200 mA
V_{CE}	20 V
P_{DISS}	7.0 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	25.0 °C/W

PACKAGE STYLE .280 4L PILL



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.055 / 26.80
C	.275 / 6.99	.285 / 7.24
D	.004 / 0.10	.006 / 0.15
E	.050 / 1.27	.060 / 1.52
F	.118 / 3.00	.130 / 3.30

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	50			V
BV_{CEO}	$I_C = 5.0$ mA	20			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 28$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	15		120	---
P_G	$V_{CC} = 18$ V $P_{OUT} = 0.2$ W $f = 1090$ MHz	10			dB